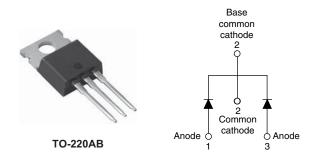
Vishay Semiconductors



Hyperfast Rectifier, 2 x 15 A FRED Pt®



PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 15 A				
V _R	300 V				
V _F at I _F	0.85 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- \bullet Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -}{\sf JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		300	V		
Average rectified forward current	per diode		T _C = 153 °C	15			
Average rectilied forward current	per device	IF(AV)		30	А		
Non-repetitive peak surge current		I _{FSM}	T _C = 25 °C	150			
Operating junction and storage temp	peratures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-		
Forward voltage	VF	I _F = 15 A	-	1.0	1.25	V	
Forward voltage	۷F	I _F = 15 A, T _J = 125 °C	-	0.85	0.95		
Deverse leekees eurrent		$V_R = V_R$ rated	-	-	40		
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	8	200	μA	
Junction capacitance	CT	V _R = 300 V	-	38	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



RoHS COMPLIANT HALOGEN FREE Available

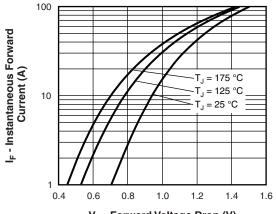
Tevision: 09-Jul-15 1 Document Number: 94016 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
		$I_{\rm F} = 1 \text{ A}, dI_{\rm F}/dt = 50$	0 A/µs, V _R = 30 V	-	-	36			
Reverse recovery time		$I_F = 1 \text{ A}, \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	-	30			
	t _{rr}	T _J = 25 °C		-	33	-	ns		
		T _J = 125 °C		-	48	-			
Deals receivers augment		T _J = 25 °C	$I_{\rm F} = 15 {\rm A}$	-	2.8	-	^		
Peak recovery current	I _{RRM} T	IRRM	IRRM	$T_J = 125 \text{ °C}$ $V_B = 200 \text{ V}$	dl _F /dt = 200 A/µs	-	6.5	-	A
	0	T _J = 25 °C	•R = 200 V	-	46	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	160	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER SYMBOL MIN. TYP. MAX. UNITS							
Maximum junction and storage temperature range	T _J , T _{Stg}	-65	-	175	°C		
Thermal resistance, junction to case per diode	R _{thJC}	-	-	1.4	°C/W		
Marking device		Case style TO-220AB 30CTH03			ГН03		



V_F - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

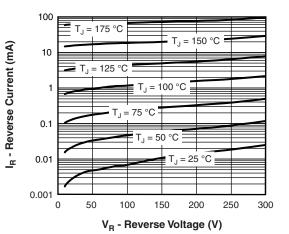
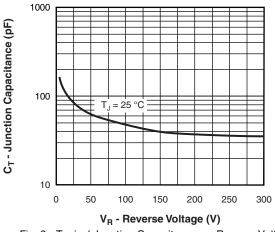


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

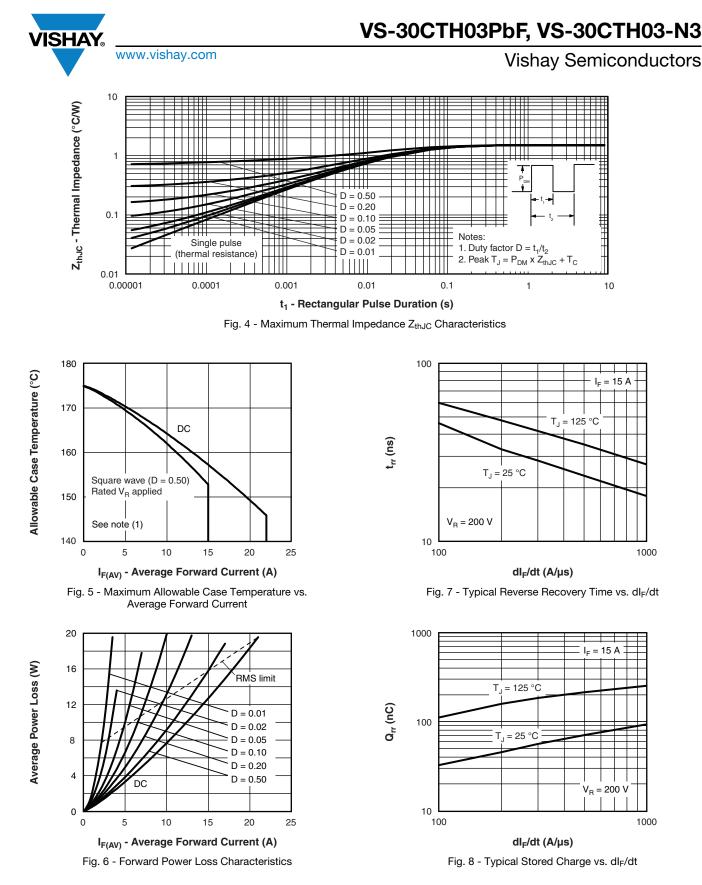




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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward power loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \text{ at } (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \text{ (see fig. 6);} \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse power loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \left(1 - \mathsf{D}\right); \mathsf{I}_{\mathsf{R}} \text{ at } \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated V}_{\mathsf{R}} \end{array}$

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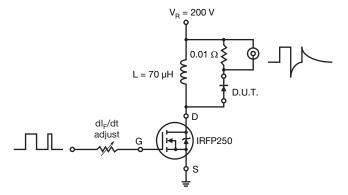
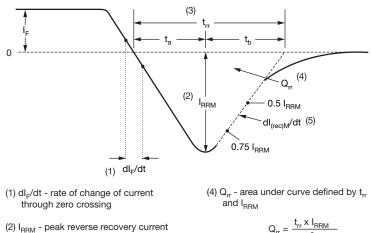
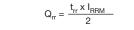


Fig. 9 - Reverse Recovery Parameter Test Circuit



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

www.vishay.com

VISHA

Device code	VS-	30	С	т	н	03	PbF
	1	2	3	4	5	6	7
	1 - 2 - 3 - 4 - 5 - 6 -	Cur Circ C = Pac T = H = Volt	rent ratii cuit confi commo kage: TO-220 hyperfa	st recov ng (03 =	: 30 A) n: de rery : 300 V)		
	7 -			ntal digit (Pb)-fre		oHS-co	ompliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-30CTH03PbF	50	1000	Antistatic plastic tube			
VS-30CTH03-N3	50	1000	Antistatic plastic tube			

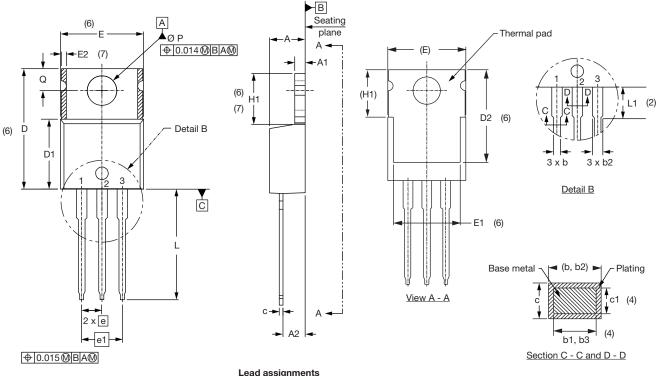
LINKS TO RELATED DOCUMENTS					
Dimensions TO-220AB www.vishay.com/doc?95222					
	TO-220ABPbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028			

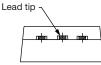


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TO-220AB

DIMENSIONS in millimeters and inches





ead.	assignments

Diodes

3. - Anode

1. - Anode/open 2. - Cathode

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed $0.127 \text{ mm} (0.005^{\circ})$ per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

SYMBOL		MILLIN	MILLIMETERS		HES	NOTES
		MIN.	MAX.	MIN.	MAX.	NOTES
Е		10.11	10.51	0.398	0.414	3, 6
E1		6.86	8.89	0.270	0.350	6
E2		-	0.76	-	0.030	7
е		2.41	2.67	0.095	0.105	
e1		4.88	5.28	0.192	0.208	
H1		6.09	6.48	0.240	0.255	6, 7
L		13.52	14.02	0.532	0.552	
L1		3.32	3.82	0.131	0.150	2
ØΡ)	3.54	3.73	0.139	0.147	
Q		2.60	3.00	0.102	0.118	
θ		90° to 93°		90° t	o 93°	
θ		90° to 93°		90° t	90° to 93°	

Conforms to JEDEC outline TO-220AB

- $^{(7)}$ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- Outline conforms to JEDEC TO-220, except A2 (maximum) and (8) D2 (minimum) where dimensions are derived from the actual package outline

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